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(54) SEMICONDUCTOR CHIP,
SEMICONDUCTOR PACKAGE INCLUDING
THE SAME, AND METHOD OF
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ABSTRACT

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A semiconductor chip, a semiconductor package including the same, and a method of fabricating the same are provided. The semiconductor chip includes an integrated circuit on a substrate, a pad electrically connected to the integrated circuit, a lower insulating structure having a contact hole exposing the pad, and a conductive pattern including a contact portion filling the contact hole, a conductive line portion provided on the lower insulating structure to extend in a specific direction, and a bonding pad portion. The contact portion has a first thickness in a direction substantially perpendicular to a top surface of the substrate and a second thickness in another direction substantially parallel to the top surface of the substrate, the first thickness is greater than the second thickness, and the lower insulating structure includes a plurality of air gaps formed therein.

